



N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
 - $25m\Omega$ @ $V_{GS} = 4.5V$
 - $29m\Omega$ @ $V_{GS} = 2.5V$
 - $36m\Omega$ @ $V_{GS} = 1.8V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

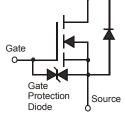
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)

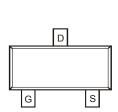








Drain



Top View

Internal Schematic

Top View

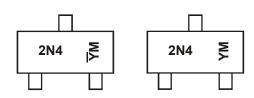
Ordering Information (Note 5)

Part Number	nber Compliance Case		Packaging	
DMG6968U-7	Standard	SOT23	3000/Tape & Reel	
DMG6968UQ-7	Automotive	SOT23	3000/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



2N4 = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or $\overline{\gamma}$ = Year (ex: A = 2013) M = Month (ex: 9 = September)

Chengdu A/T Site

Shanghai A/T Site

Date Code Kev

Year	2009	9	2010		2011	20	12	2013		2014	2	2015
Code	W		X		Υ	2	7	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characte	eristic		Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6)	T _A = +25°C T _A = +70°C	I _D	6.5 5.2	А	
Pulsed Drain Current			I _{DM}	30	Α

Thermal Characteristics

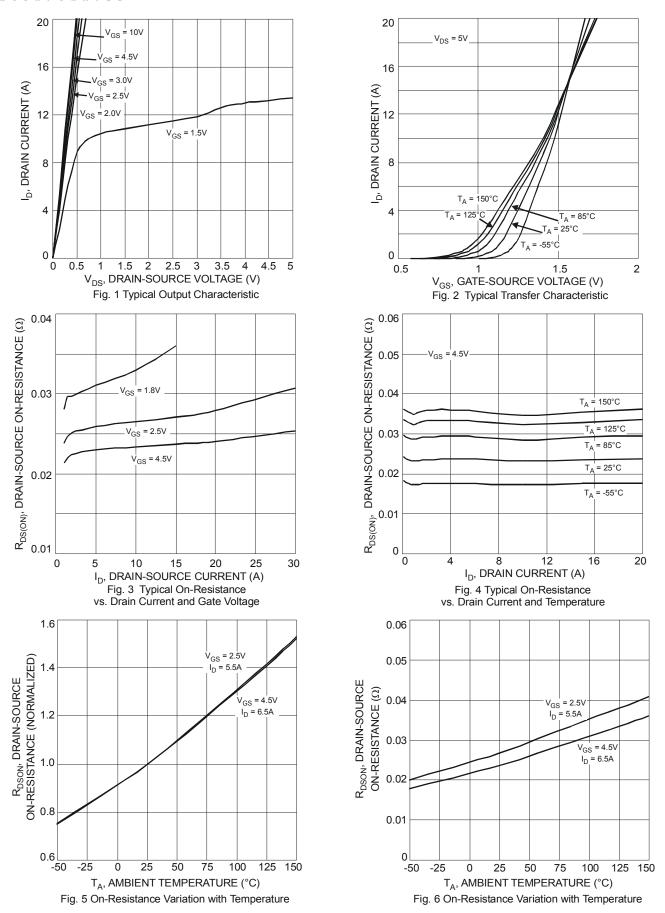
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	1.3	W
Thermal Resistance, Junction to Ambient @ T _A = +25°C	$R_{\theta JA}$	157	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Syllibol	IVIIII	Тур	IVIAX	Onit	rest Condition		
•	D) /	20	1	1	.,	N/ 01/ 1 050: A		
Drain-Source Breakdown Voltage		BV _{DSS}	20	_		V	V _{GS} = 0V, I _D = 250μA	
Zero Gate Voltage Drain Current	$T_J = +25^{\circ}C$	I _{DSS}	_	—	1.0	μA	V _{DS} = 20V, V _{GS} = 0V	
Gate-Source Leakage		I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 10V$, $V_{DS} = 0V$	
Gate-Source Breakdown Voltage		BV _{SGS}	±12	_	_	V	$V_{DS} = 0V, I_{G} = \pm 250 \mu A$	
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage		V _{GS(th)}	0.5	_	0.9	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			_	21	25		V _{GS} = 4.5V, I _D = 6.5A	
Static Drain-Source On-Resistance		R _{DS(ON)}		23	29	mΩ	V _{GS} = 2.5V, I _D = 5.5A	
				28	36		V _{GS} = 1.8V, I _D = 3.5A	
Forward Transfer Admittance			_	8	_	S	V _{DS} = 10V, I _D = 5A	
DYNAMIC CHARACTERISTICS (Note 8))							
Input Capacitance		C _{iss}	_	151	_	pF		
Output Capacitance		Coss	_	91	_	pF	$V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance		Crss	_	32	_	pF	1.500112	
Total Gate Charge		Qg	_	8.5	_	nC		
Gate-Source Charge		Q _{gs}	_	1.6	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6.5A$	
Gate-Drain Charge		Q_{gd}	_	2.8	_	nC		
Turn-On Delay Time		t _{D(on)}	_	54	_	ns		
Turn-On Rise Time		t _r	_	66	_	ns	V _{DD} = 10V, V _{GS} = 4.5V,	
Turn-Off Delay Time		t _{D(off)}	_	613	_	ns	$R_L = 10\Omega$, $R_G = 6\Omega$, $I_D = 1A$	
Turn-Off Fall Time	t _f	_	205	_	ns			

6. Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal vias to bottom layer 1 inch square copper plate.7. Short duration pulse test used to minimize self-heating effect.8. Guaranteed by design. Not subject to production testing. Notes:







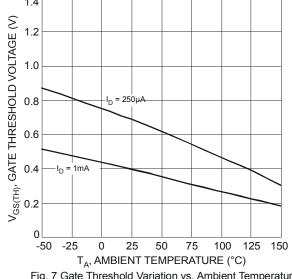
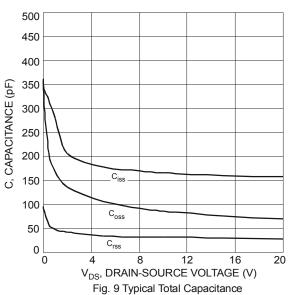
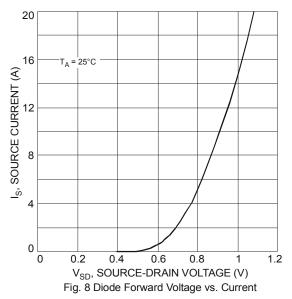


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





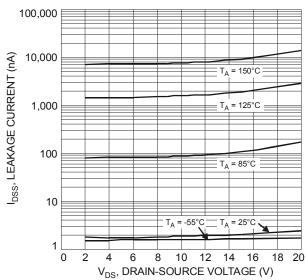


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

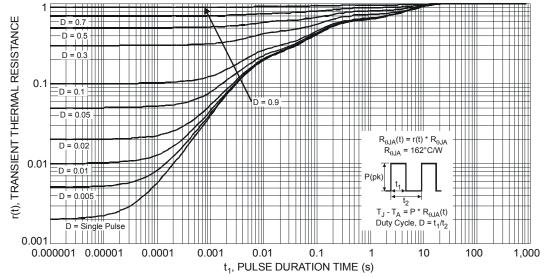
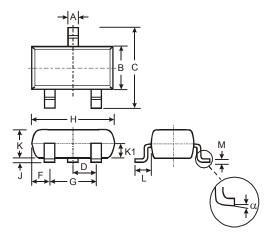


Fig. 11 Transient Thermal Response



Package Outline Dimensions

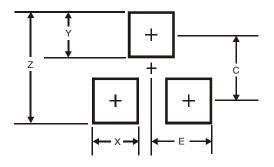
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
М	0.085	0.18	0.11				
α	0°	8°	-				
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)			
Z	2.9			
X	0.8			
Y	0.9			
С	2.0			
F	1.35			



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2013, Diodes Incorporated

www.diodes.com

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Diodes Incorporated:

DMG6968UQ-7